

## ABSTRACT OF THE DISCLOSURE

A polishing slurry including an abrasive, deionized water, a pH controlling agent, and polyethylene imine, can control the removal rates of a silicon oxide layer and a silicon nitride layer which are simultaneously exposed during chemical mechanical polishing (CMP) of a conductive layer. A relative ratio of the removal rate of the silicon oxide layer to that of the silicon nitride layer can be controlled by controlling an amount of the choline derivative.

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